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Ann-Ellice Parker

Ann-Ellice Parker

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: MOK et al.

Docket No.: NNEX0012C

Serial No.: 10/717, 813

Art Unit: 2829

Filed: 11/19/2003

Examiner: Unknown

Title: MOSAIC DECAL PROBE

OCTOBER 22, 2004

TRANSMITTAL FORM

Commissioner of Patents
Mail Stop IDS
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The following documents are being transmitted:

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- Information Disclosure Statement, (2 pgs) 1449 form
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- Cited References

Applicant believes that there is no fee due with this submission. However, the Commissioner is authorized to charge any additional fees that may be due and credit any overpayments to Deposit Account No. 07-1445 (Order No. NNEX0012C). A copy of this sheet is enclosed for accounting purposes.

Respectfully submitted,

Michael A. Glenn

Michael A. Glenn
Reg. No. 30,176

Customer No. 22862



CERTIFICATE OF TRANSMISSION UNDER 37 C.F.R. §1.10

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Ann-Ellice Parker
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: MOK, et al.

Docket No.: NNEX0012C

Serial No. : 10/717,813

Art Unit: 2829

Filed: November 19, 2003

Examiner: Unknown

Title: MOSAIC DECAL PROBE

Assistant Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450
October 22, 2004

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is submitted:

☒ (X) under 37 CFR 1.97(b), or

(within three months of filing national application; or date of entry of international application; or before mailing date of first office action on the merits; whichever occurs last)

under 37 CFR 1.97(c) together with either a:

☐ () Certification under 37 CFR 1.97(e), or

☐ () a \$220.00 fee under 37 CFR 1.17(p), or

(After the CFR 1.97(b) time period, but before final action or notice of allowance, whichever occurs first)

☐ () under 37 CFR 1.97(d) together with a:

☐ () Certification under 37 CFR 1.97(e), and

☐ () a \$220.00 fee under 37 CFR 1.17(d)(2)(ii), and

☐ () a \$130.00 petition fee set forth in 37 CFR 1.17(i)(1)

(Filed after final action or notice of allowance, whichever occurs first, but before payment of the issue fee)

☒ (X) The Commissioner is authorized to charge any additional fees or credit any overpayment to Deposit Account No. 07-1445 (Order No. NNEX0012C). A copy of this sheet is enclosed for accounting purposes.

☒ (X) Applicant(s) submit herewith Form PTO 1449 -- Information Disclosure Citation together with copies of patents, publications or other information of which applicant(s)

are aware, which applicant(s) believe(s) may be material to the examination of this application and for which there may be a duty to disclose in accordance with 37 CFR 1.25.

() A concise explanation of the relevance of foreign language patents, foreign language publications and other foreign language information listed on PTO Form 1449, as presently understood by the individual(s) designated in 37 CFR 156(c) most knowledgeable about the content is given on the attached sheet, or where a foreign language patent is cited in a search report or other action by a foreign patent office in a counterpart foreign application, an English language version of the search report or action which indicates the degree of relevance found by the foreign office is listed on form PTO 1449 and is enclosed herewith.

It is requested that the information disclosed herein be made of record in this application.

Respectfully Submitted,



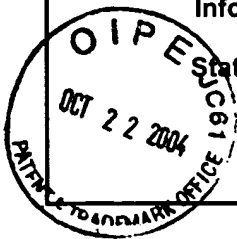
Michael Glenn
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Form 1449 (Modified)

Information Disclosure

Statement By Applicant



Atty. Docket No.: NNEX0012C Serial No.: 10/717, 813

Applicant: Mok et al

Examiner:
UnassignedFiling Date: November 19,
2003

Group: 2829

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